Vishay Semiconductors

Hyperfast Rectifier, 20 A FRED Pt[®] G5



LINKS TO ADDITIONAL RESOURCES



| PRIMARY CHARACTERISTICS | | | | | | | | | |
|--|-------------------------------------|--|--|--|--|--|--|--|--|
| I _{F(AV)} | 20 A | | | | | | | | |
| V _R | 1200 V | | | | | | | | |
| V _F at I _F at 125 °C | 1.88 V | | | | | | | | |
| t _{rr} | 37 ns | | | | | | | | |
| T _J max. | 175 °C | | | | | | | | |
| Package | D ² PAK 2L (TO-263AB 2L) | | | | | | | | |
| Circuit configuration | Single | | | | | | | | |

FEATURES

- Minimum creepage and clearance distances are 5.2 mm and 5.4 mm respectively
- Hyperfast and optimized Qrr
- Best in class forward voltage drop and switching
 HALOGEN
 FREE
 losses trade off
- Optimized for high speed operation
- 175 °C maximum operating junction temperature
- Polyimide passivation
- Meets MSL level 1, per J-STD-020, LF maximum peak of 245 °C
- AEC-Q101 qualified meets JESD 201 class 2 whisker test
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

DESCRIPTION / APPLICATIONS

Featuring a unique combination of low conduction and switching losses, this rectifier is the right choice for high frequency converters, both soft switched / resonant. Specifically designed to improve efficiency of PFC and output rectification stages of EV / HEV battery charging stations, booster stage of solar inverters and UPS applications, these devices are perfectly matched to operate with MOSFETs or high speed IGBTs.

MECHANICAL DATA

Case: D²PAK 2L (TO-263AB 2L)

Molding compound meets UL 94 V-0 flammability rating

Terminals: matte tin plated leads, solderable per J-STD-002

| ABSOLUTE MAXIMUM RATINGS | | | | | | | | | | |
|--|-----------------------------------|---|-------------|-------|--|--|--|--|--|--|
| PARAMETER | SYMBOL | TEST CONDITIONS | VALUES | UNITS | | | | | | |
| Repetitive peak reverse voltage | V _{RRM} | | 1200 | V | | | | | | |
| Average rectified forward current | I _{F(AV)} | T _C = 103 °C | 20 | | | | | | | |
| Repetitive peak forward current | I _{FRM} | T _C = 103 °C, D = 0.50, f = 20 kHz | 32 | А | | | | | | |
| Non-repetitive peak surge current | I _{FSM} | T_{C} = 45 °C, t_{p} = 10 ms, sine wave | 125 | | | | | | | |
| Operating junction and storage temperature | T _J , T _{Stg} | | -55 to +175 | °C | | | | | | |

| ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified) | | | | | | | | | | | |
|---|-------------------------------------|---|------|------|------|-------|--|--|--|--|--|
| PARAMETER | SYMBOL | TEST CONDITIONS | MIN. | TYP. | MAX. | UNITS | | | | | |
| Breakdown voltage, blocking voltage | V _{BR} , V _R | I _R = 100 μA | 1200 | - | - | | | | | | |
| Forward voltage | V _F | I _F = 20 A | - | 2.04 | 2.66 | V | | | | | |
| Torward voltage | | I _F = 20 A, T _J = 125 °C | - | 1.88 | - | | | | | | |
| Poveros loskago ourrent | 1 | $V_{R} = V_{R}$ rated | - | - | 50 | | | | | | |
| Reverse leakage current | I _R | $T_J = 125 \text{ °C}, V_R = V_R \text{ rated}$ | - | - | 500 | μA | | | | | |
| Junction capacitance | CT | V _R = 200 V | - | 10 | - | pF | | | | | |
| Series inductance | L _S | Measured to lead 5 mm from package body | - | 8 | - | nH | | | | | |

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COMPLIANT







www.vishay.com

| DYNAMIC RECOVERY CHARACTERISTICS (T_J = 25 °C unless otherwise specified) | | | | | | | | | | |
|---|------------------|---------------------------------------|---|------|------|------|-------|--|--|--|
| PARAMETER | SYMBOL | TEST | CONDITIONS | MIN. | TYP. | MAX. | UNITS | | | |
| | | $I_F = 1.0 \text{ A}, \text{ d}I_F/c$ | It = 100 A/ μ s, V _R = 30 V | - | 37 | - | | | | |
| Reverse recovery time | t _{rr} | T _J = 25 °C | | - | 125 | - | ns | | | |
| | | T _J = 125 °C | | - | 188 | - | 115 | | | |
| Peak recovery current | 1 | T _J = 25 °C | $I_{\rm F} = 12 {\rm A}$ | - | 14 | - | A | | | |
| reak recovery current | I _{RRM} | T _J = 125 °C | dI _F /dt = 600 A/µs V _R = 400 V | - | 19 | - | | | | |
| Reverse recovery charge | Q _{rr} | T _J = 25 °C | | - | 670 | - | nC | | | |
| neverse recovery charge | | T _J = 125 °C | | - | 1450 | - | | | | |
| Bevere recevery time | + | T _J = 25 °C | | - | 90 | - | ns | | | |
| Reverse recovery time | t _{rr} | T _J = 125 °C | | - | 107 | - | | | | |
| Deels receivers ourrent | | T _J = 25 °C | $I_{\rm F} = 20 {\rm A}$ | - | 28 | - | A | | | |
| Peak recovery current | I _{RRM} | T _J = 125 °C | dI _F /dt = 1000 A/µs V _B = 800 V | - | 48 | - | | | | |
| | 0 | T _J = 25 °C | | - | 1450 | - | | | | |
| Reverse recovery charge | Q _{rr} | T _J = 125 °C | | - | 2930 | - | nC | | | |

| THERMAL - MECHANICAL SPECIFICATIONS | | | | | | | | | | |
|--|-----------------------------------|--|------------|------|------|-------|--|--|--|--|
| PARAMETER | SYMBOL | TEST CONDITIONS | MIN. | TYP. | MAX. | UNITS | | | | |
| Thermal resistance, junction-to-case | R _{thJC} | | - | - | 1.7 | °C/W | | | | |
| Weight | | | - | 2.0 | - | g | | | | |
| Maximum junction and storage temperature range | T _J , T _{Stg} | | -55 | - | 175 | °C | | | | |
| Marking device | | Case style D ² PAK 2L (TO-263AB 2L) | E5TH2112SH | | | | | | | |

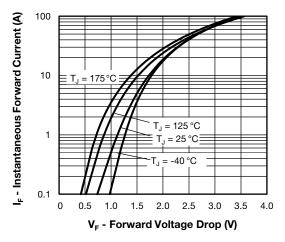


Fig. 1 - Forward Voltage Drop Characteristics

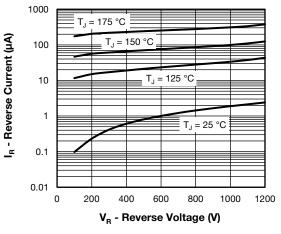


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage



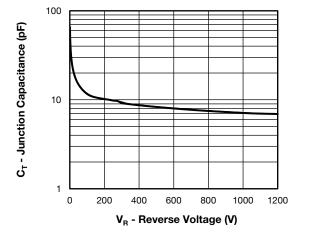


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

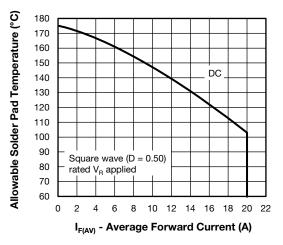


Fig. 4 - Maximum Allowable Case Temperature vs. Average Forward Current

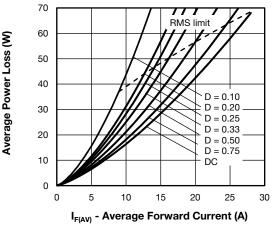


Fig. 5 - Forward Power Loss Characteristics

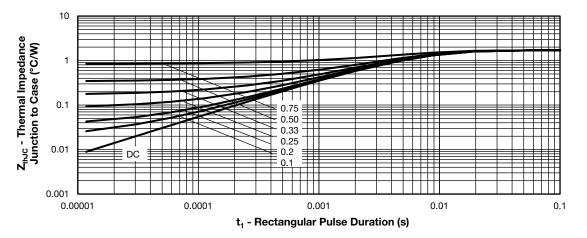


Fig. 6 - Transient Thermal Impedance, Junction to Case

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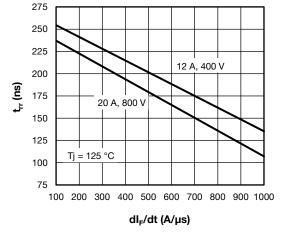
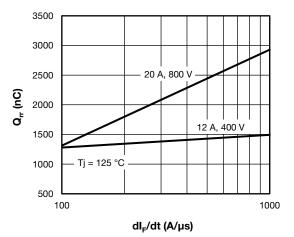
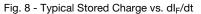


Fig. 7 - Typical Reverse Recovery Time vs. dl_F/dt





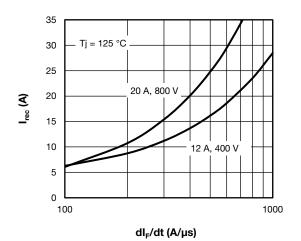


Fig. 9 - Typical Stored Charge vs. dl_F/dt



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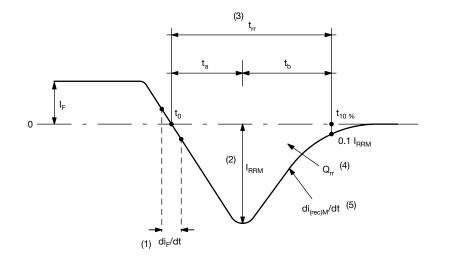


Fig. 10 - Reverse Recovery Waveform and Definitions

Notes

- $^{(1)}~di_{F}/dt$ rate of change of current through zero crossing
- ⁽²⁾ I_{RRM} peak reverse recovery current
- ⁽³⁾ t_{rr} reverse recovery time measured from t_0 , crossing point of negative going I_F, to point $t_{10\%}$, 0.1 I_{RRM} ⁽⁴⁾ Q_{rr} - area under curve defined by t_0 and $t_{10\%}$

$$Q_{rr} = \int_{t_0}^{t_{10\%}} I(t)dt$$

⁽⁵⁾ di_(rec)M/dt - peak rate of change of current during t_b portion of t_{rr}

ORDERING INFORMATION TABLE

I

| Device code | VS- | Е | 5 | т | н | 21 | 12 | S2 | L | н | МЗ |
|-------------|---|---|-----------|------------------------|----------|---------|----------|---------|-----------|-----------|------|
| | | 2 | 3 | 4 | 5 | 6 | 7 | 8 | 9 | 10 | (11) |
| | 1 - Vishay Semiconductors product | | | | | | | | | | |
| | 2 - E = single diode | | | | | | | | | | |
| | 3 - 5 = FRED generation 5 | | | | | | | | | | |
| | 4 - Package: | | | | | | | | | | |
| | | T = TO-263 / D ² PAK package | | | | | | | | | |
| | 5 | • H= | hyperfa | ast recov | very | | | | | | |
| | 6 | - Cur | rent rati | ng (21 = | = 20 A) | | | | | | |
| | 7 · | · Vol | tage rati | ing (12 = | = 1200 \ | /) | | | | | |
| | 8 | - S2 | = true 2 | pin D ² F | PAK | | | | | | |
| | 9 - None = tube (50 pieces) | | | | | | | | | | |
| | L = tape and reel (left oriented, for D²PAK package) | | | | | | | | | | |
| | If needed different orientation/packaging, please contact factory | | | | | | | | | / | |
| | 10 - H = AEC-Q101 qualified | | | | | | | | | | |
| | 11 · | | | ntal digit en-free, | | complia | ant, and | termina | ation lea | ıd (Pb)-i | free |

 ORDERING INFORMATION (Example)

 PREFERRED P/N
 BASE QUANTITY
 PACKAGING DESCRIPTION

 VS-E5TH2112S2LHM3
 800
 13" diameter reel

| LINKS TO RELATED DOCUMENTS | | | | | | | | |
|----------------------------|--------------------------|--|--|--|--|--|--|--|
| Dimensions | www.vishay.com/doc?96683 | | | | | | | |
| Part marking information | www.vishay.com/doc?96693 | | | | | | | |
| Packaging information | www.vishay.com/doc?95032 | | | | | | | |

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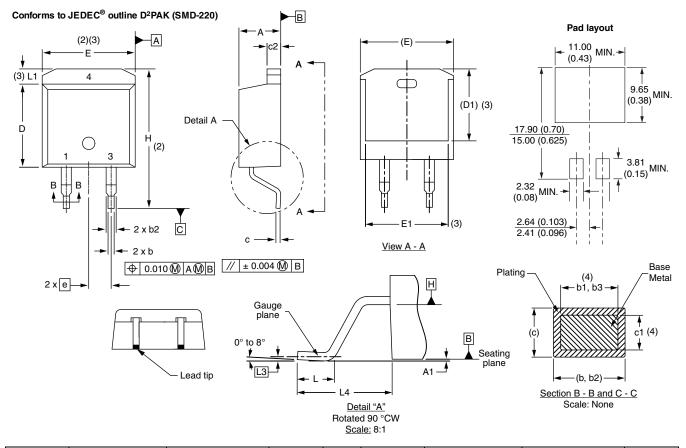
VS-E5TH2112S2LHM3

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D²PAK 2L (TO-263AB 2L)

DIMENSIONS in millimeters and inches



| SYMBOL | MILLIMETERS | | INCHES | | NOTES | NOTES | | NOTES | | MILLIM | ETERS | INC | HES | NOTES |
|--------|-------------|-------|--------|-------|-------|--------|------|-------|-------|--------|-------|------|-----|-------|
| STMBOL | MIN. | MAX. | MIN. | MAX. | NOTES | SYMBOL | MIN. | MAX. | MIN. | MAX. | NOTES | | | |
| А | 4.06 | 4.83 | 0.160 | 0.190 | | | D1 | 6.86 | 8.00 | 0.270 | 0.315 | 3 | | |
| A1 | 0.00 | 0.254 | 0.000 | 0.010 | | | E | 9.65 | 10.67 | 0.380 | 0.420 | 2, 3 | | |
| b | 0.51 | 0.99 | 0.020 | 0.039 | | | E1 | 7.90 | 8.80 | 0.311 | 0.346 | 3 | | |
| b1 | 0.51 | 0.89 | 0.020 | 0.035 | 4 | | е | 2.54 | BSC | 0.100 | BSC | | | |
| b2 | 1.14 | 1.78 | 0.045 | 0.070 | | | Н | 14.61 | 15.88 | 0.575 | 0.625 | | | |
| b3 | 1.14 | 1.73 | 0.045 | 0.068 | 4 | | L | 1.78 | 2.79 | 0.070 | 0.110 | | | |
| с | 0.38 | 0.74 | 0.015 | 0.029 | | | L1 | - | 1.65 | - | 0.066 | 3 | | |
| c1 | 0.38 | 0.58 | 0.015 | 0.023 | 4 | | L3 | 0.25 | BSC | 0.010 | BSC | | | |
| c2 | 1.14 | 1.65 | 0.045 | 0.065 | | | L4 | 4.78 | 5.28 | 0.188 | 0.208 | | | |
| D | 8.51 | 9.65 | 0.335 | 0.380 | 2 | | | | | | | | | |

Notes

⁽¹⁾ Dimensioning and tolerancing per ASME Y14.5 M-1994

(2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
 (3) Thermal and contain antional within dimension E 1.1, D1 and E1.

⁽³⁾ Thermal pad contour optional within dimension E, L1, D1 and E1

⁽⁴⁾ Dimension b1 and c1 apply to base metal only

⁽⁵⁾ Datum A and B to be determined at datum plane H

⁽⁶⁾ Controlling dimension: inch

(7) Outline conforms to JEDEC® outline TO-263AB

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